

NVTFS4C08N

MOSFET – Power, Single N-Channel, μ 8FL 30 V, 5.9 m Ω , 55 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- NVTFS4C08NWF – Wettable Flanks Product
- NVT Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 4)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	17	A
		$T_A = 100^{\circ}\text{C}$		12	
$T_A = 25^{\circ}\text{C}$		P_D	3.1	W	
$T_A = 100^{\circ}\text{C}$			1.6		
Continuous Drain Current $R_{\theta JC}$ (Note 1, 3, 4)		$T_A = 25^{\circ}\text{C}$	I_D	55	
		$T_A = 100^{\circ}\text{C}$		39	A
Power Dissipation $R_{\theta JC}$ (Note 1, 3, 4)		$T_A = 25^{\circ}\text{C}$	P_D	31	W
		$T_A = 100^{\circ}\text{C}$		15	
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$, $t_p = 10\ \mu\text{s}$	I_{DM}	253	A	
Operating Junction and Storage Temperature			T_J , T_{stg}	-55 to +175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	28	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^{\circ}\text{C}$, $I_L = 20\ A_{pk}$, $L = 0.1\ \text{mH}$)			E_{AS}	20	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Drain) (Notes 1 and 4)	$R_{\theta JC}$	4.9	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Notes 1 and 2)	$R_{\theta JA}$	48	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm² 2 oz. Cu pad.
3. Assumes heat-sink sufficiently large to maintain constant case temperature independent of device power.
4. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

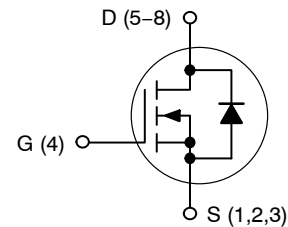


ON Semiconductor®

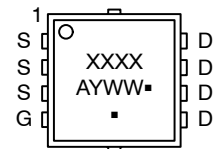
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	5.9 m Ω @ 10 V	55 A
	9.0 m Ω @ 4.5 V	

N-Channel MOSFET



MARKING DIAGRAM



4C08 = Specific Device Code for NVMTS4C08N

08WF = Specific Device Code of NVTFS4C08NWF

A = Assembly Location

Y = Year

WW = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NVTFS4C08N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			13.8		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 24 V			1.0	μA
					10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.3		2.2	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			5.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		4.7	5.9	mΩ
		V _{GS} = 4.5 V, I _D = 18 A		7.2	9.0	
Forward Transconductance	g _{FS}	V _{DS} = 1.5 V, I _D = 15 A		42		S
Gate Resistance	R _G	T _A = 25°C		1.0		Ω

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 15 V		1113		pF
Output Capacitance	C _{OSS}			702		
Reverse Transfer Capacitance	C _{RSS}			39		
Capacitance Ratio	C _{RSS} /C _{ISS}	V _{GS} = 0 V, V _{DS} = 15 V, f = 1 MHz		0.035		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V; I _D = 30 A		8.4		nC
Threshold Gate Charge	Q _{G(TH)}			1.8		
Gate-to-Source Charge	Q _{GS}			3.5		
Gate-to-Drain Charge	Q _{GD}			3.3		
Gate Plateau Voltage	V _{GP}			3.4		V
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 15 V; I _D = 30 A		18.2		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 15 A, R _G = 3.0 Ω		9.0		ns
Rise Time	t _r			33		
Turn-Off Delay Time	t _{d(OFF)}			15		
Fall Time	t _f			4.0		
Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 15 V, I _D = 15 A, R _G = 3.0 Ω		7.0		ns
Rise Time	t _r			26		
Turn-Off Delay Time	t _{d(OFF)}			19		
Fall Time	t _f			3.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 10 A	T _J = 25°C		0.79	1.1	V
			T _J = 125°C		0.66		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 30 A		28.3		ns	
Charge Time	t _a			14.5			
Discharge Time	t _b			13.8			
Reverse Recovery Charge	Q _{RR}			15.3		nC	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

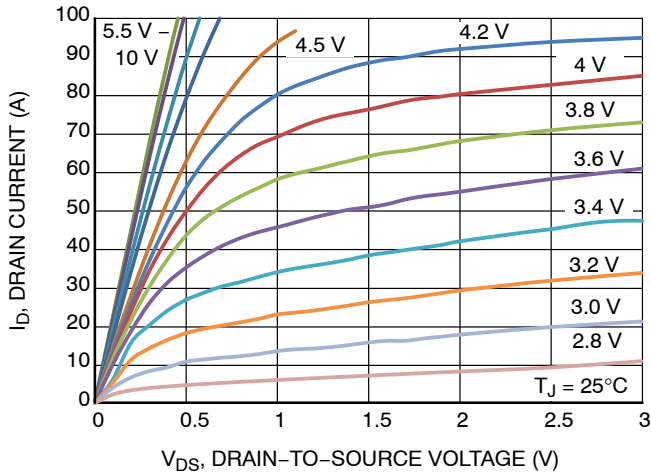


Figure 1. On-Region Characteristics

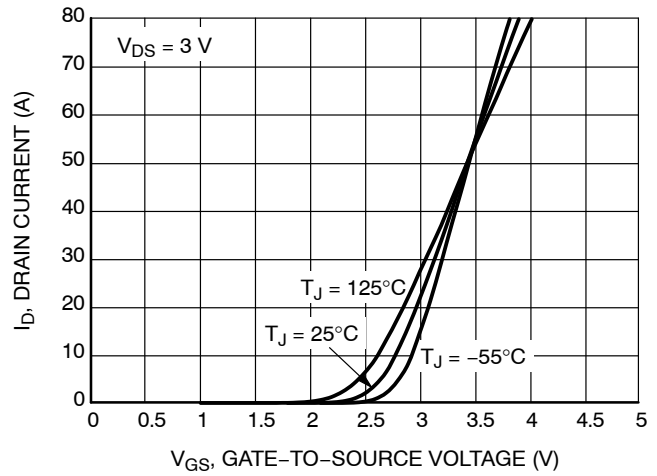


Figure 2. Transfer Characteristics

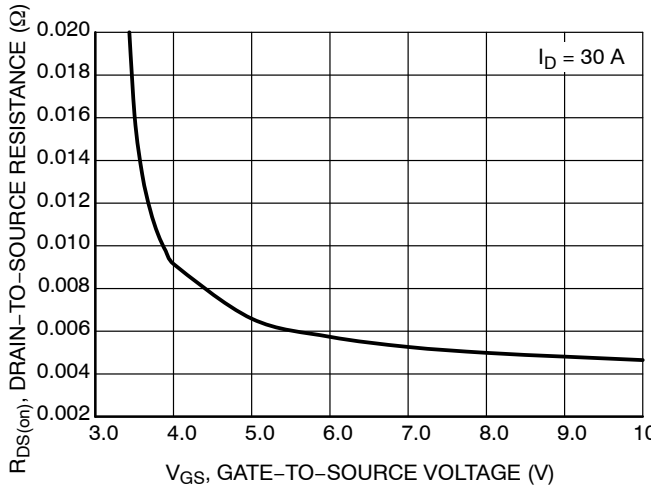


Figure 3. On-Resistance vs. V_{GS}

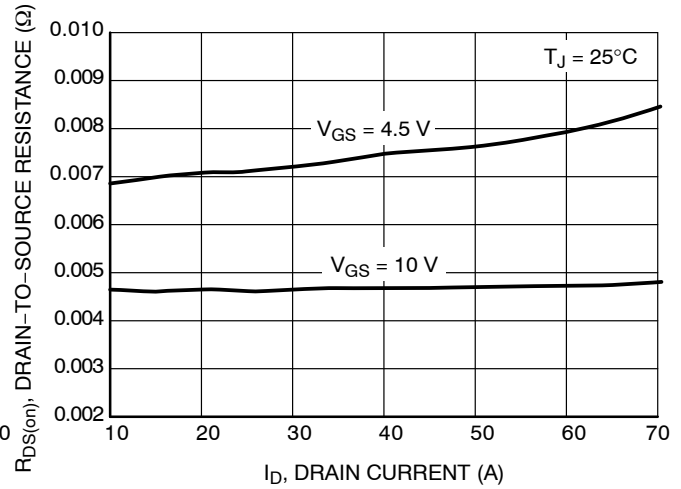


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

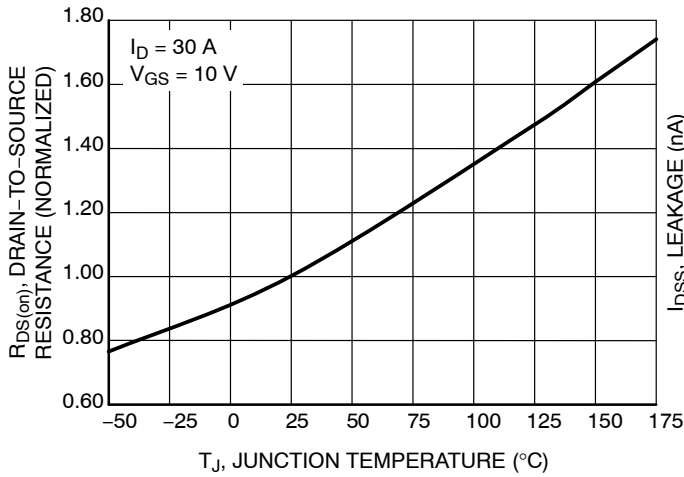


Figure 5. On-Resistance Variation with Temperature

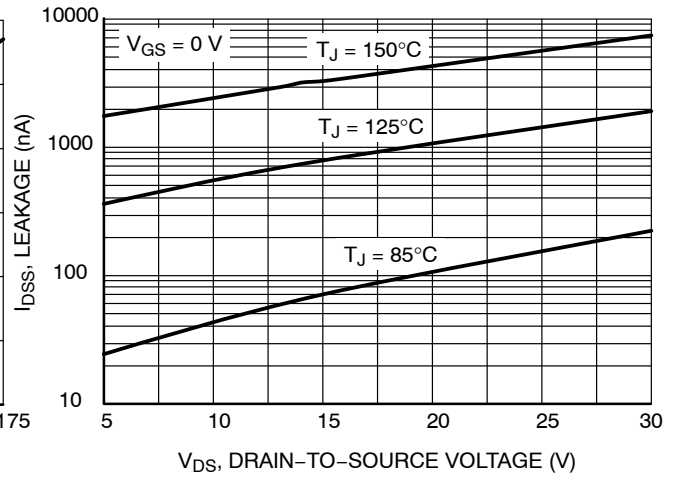


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

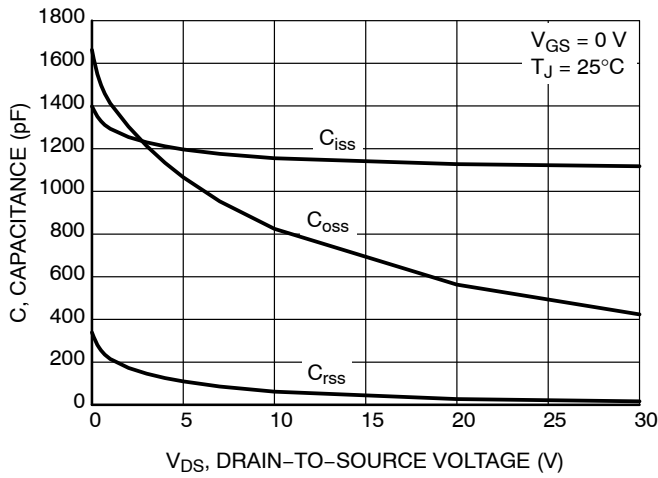


Figure 7. Capacitance Variation

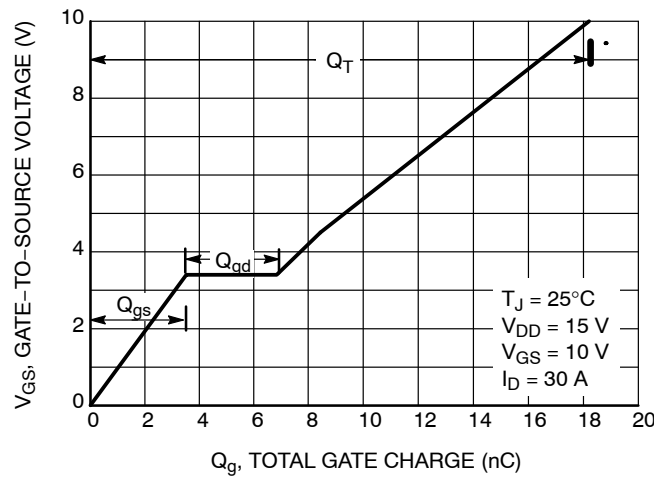


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

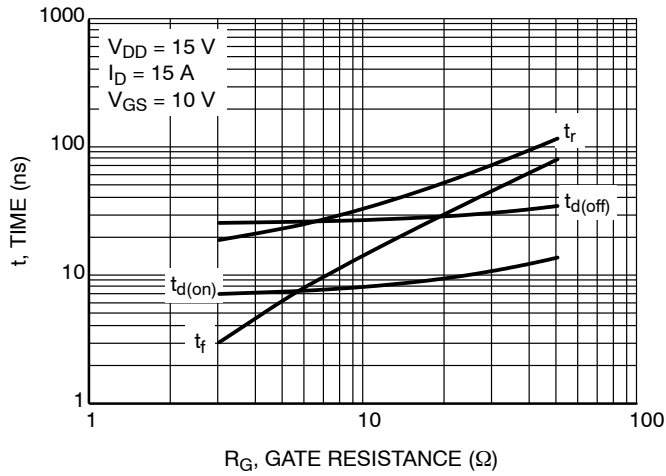


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

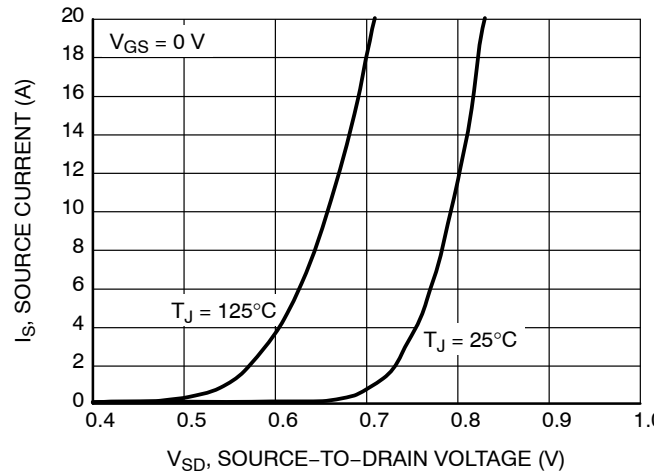


Figure 10. Diode Forward Voltage vs. Current

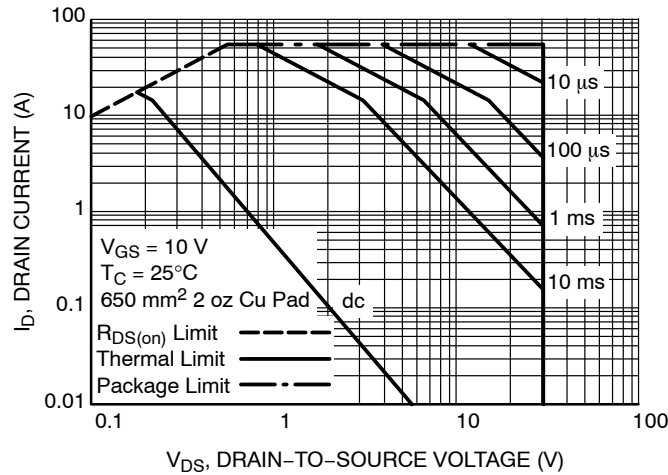


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NVTFS4C08N

TYPICAL CHARACTERISTICS

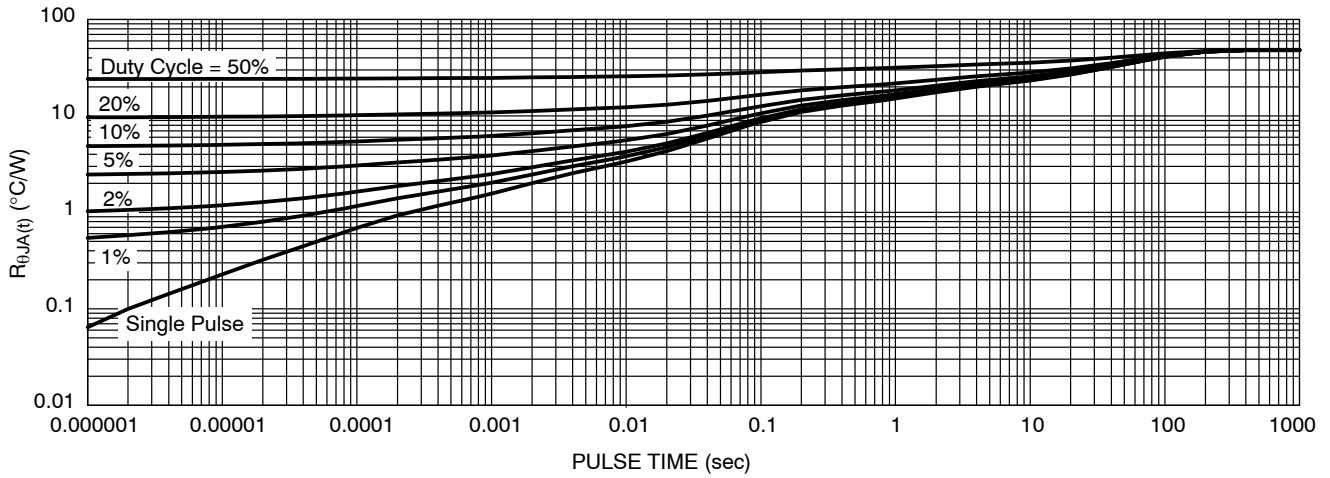


Figure 12. Thermal Response

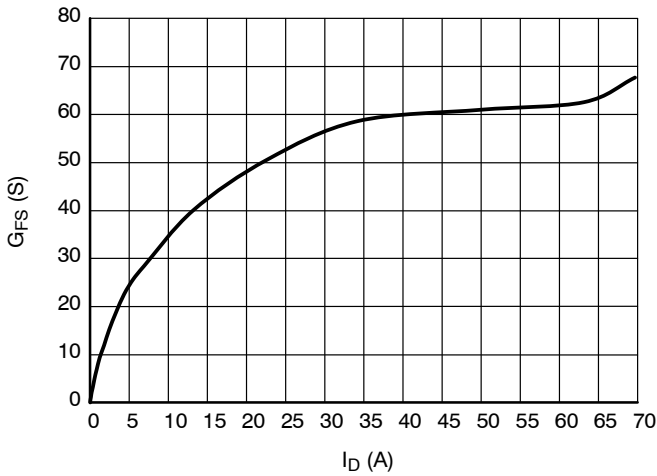


Figure 13. G_{FS} vs. I_D

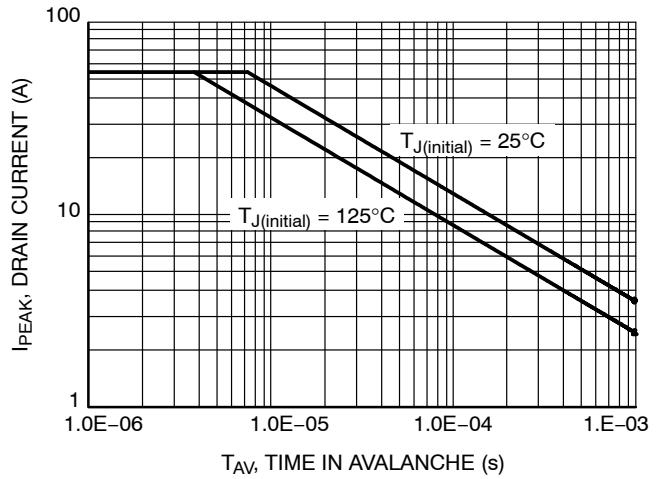


Figure 14. Avalanche Characteristics

ORDERING INFORMATION

Device	Package	Shipping [†]
NVTFS4C08NTAG	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFS4C08NWFTAG	WDFN8 (Pb-Free)	1500 / Tape & Reel
NVTFS4C08NTWG	WDFN8 (Pb-Free)	5000 / Tape & Reel
NVTFS4C08NWFTWG	WDFN8 (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

